TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

# MT6L62AT

VHF-UHF Band Low Noise Amplifier Application

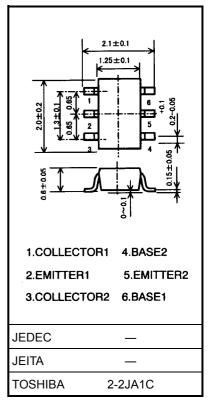
VHF-UHF Band Oscillator Application

#### Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rat	Unit		
Characteristics		Q1	Q2	Onit	
Collector-base voltage	V <sub>CBO</sub>	10	10	V	
Collector-emitter voltage	V <sub>CEO</sub>	5	5	V	
Emitter-base voltage	V <sub>EBO</sub>	1.5 2		V	
Collector current	Ι <sub>C</sub>	25	40	mA	
Base current	Ι <sub>Β</sub>	10	10	mA	
Collector power dissipation	P <sub>C</sub>	200		mW	
	(Note1)				
Junction temperature	Tj	125		°C	
Storage temperature range	T <sub>stg</sub>	-55~125		°C	

Note1: Total power dissipation of Q1 and Q2

	Q1	Q2
Three pin SSM type part No.	MT3S07S	MT3S03AS



Weight: 0.008 g (typ.)

Unit: mm

## Electrical Characteristics Q1-Side (Ta = 25°C)

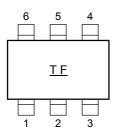
Characteristics	Symbol	Test Condition		Тур.	Max	Unit	
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = 5 \text{ V}, \text{ I}_{E} = 0$		_	0.1	μA	
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = 1 V, I_C = 0$	—	—	1	μA	
DC current gain	h <sub>FE</sub>	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$	70	—	140	—	
Transition frequency	f <sub>T</sub>	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 10 \text{ mA}$	10	12		GHz	
Insertion gain	S <sub>21e</sub>   <sup>2</sup> (1)	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 2 \text{ GHz}$		7		dB	
	S <sub>21e</sub>   <sup>2</sup> (2)	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 15 \text{ mA}, \text{ f} = 2 \text{ GHz}$	6.5	8.5			
Noise figure	NF (1)	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 2 \text{ GHz}$		1.6	3	dB	
	NF (2)	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 2 \text{ GHz}$		1.5	3		
Reverse transfer capacitance	C <sub>re</sub>	$V_{CB}=1 \ V, \ I_E=0, \ f=1 \ MHz \tag{Note2}$	_	0.45	0.85	pF	

# Electrical Characteristics Q2-Side (Ta = 25°C)

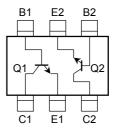
Characteristics	Symbol	Test Condition		Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = 5 V, I_E = 0$		_	0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = 1 V, I_{C} = 0$			1	μA
DC current gain	h <sub>FE</sub>	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$		_	160	
Transition frequency	f <sub>T</sub> (1)	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$	5	7		GHz
	f <sub>T</sub> (2)	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 10 \text{ mA}$	7	10		
Insertion gain	S <sub>21e</sub>   <sup>2</sup> (1)	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 2 \text{ GHz}$	_	5		dB
	S <sub>21e</sub>   <sup>2</sup> (2)	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 20 \text{ mA}, \text{ f} = 2 \text{ GHz}$	3	6.5		
Noise figure	NF (1)	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 2 \text{ GHz}$		1.7	3	dB
	NF (2)	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 7 \text{ mA}, \text{ f} = 2 \text{ GHz}$	_	1.4	2.2	ub
Reverse transfer capacitance	C <sub>re</sub>	$V_{CB} = 1 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$ (Note2)	_	0.8	1.15	pF

Note2: C<sub>re</sub> is measured by 3 terminal method with capacitance bridge.

#### Marking



### Pin Assignment (top view)



#### Caution

This device electrostatic sensitivity. Please handle with caution.

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